EE 330

Assignment 13

Spring 2018

Since there will be an in-class exam on Friday April 13, this assignment will not be collected or graded.

If references to a semiconductor processes are needed beyond what is given in a specific problem or question, assume a CMOS process is available with the following key process parameters;  $\mu_n C_{OX} = 350 \mu A/v^2$ ,  $\mu_p C_{OX} = 70 \mu A/v^2$ ,  $V_{TNO} = 0.5 V$ ,  $V_{TPO} = -0.5 V$ ,  $C_{OX} = 4fF/\mu^2$ ,  $L_{MIN} = W_{MIN} = 0.18$ , and  $V_{DD} = 2.0 V$  and a bipolar process is available with model parameters  $J_S = 10^{-14} A/u^2$ ,  $\beta_n = 100$  and  $\beta_p = 40$ . The output conductance of the BJT and the MOSFET are characterized, respectively, by  $V_{AF} = 100 V$  and  $\lambda = .01 V^{-1}$ .

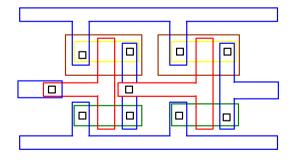
**Problem 1** A standard CMOS inverter is shown below. If the devices are sized so that  $W_1=W_2=1u$ ,  $L_1=L_2=1u$ , determine the trip point if  $V_{DD}=2.05V$ .

**Problem 2** What percent deviation in the trip point voltage for the circuit of Problem 1 will occur if the magnitude of the n-channel threshold voltage decreases by 20% and the magnitude of the p-channel threshold voltage increases by 20% from the nominal value?

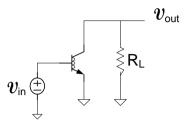
**Problem 3** Give all of the two-input Boolean functions and identify which of those are useful or are actually used.

**Problem 4** A physical layer implementation of a circuit at the layout level is shown below where blue denotes metal, red polysilicon, and green n-active, yellow p-active, brown n-well and black contacts. Assume the upper metal rail is a VDD pin, the lower metal rail is ground, the middle left metal is Boolean input A, and the middle right metal is Boolean output B.

- a) Give a physical layer view of this layout at the circuit schematic level. Assume the contact sizes are  $2\lambda x + 2\lambda$ .
- b) Give a structural layer view of this layout at the gate level.

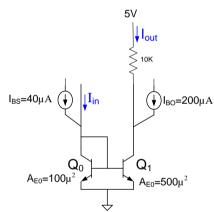


**Problem 5** The small-signal equivalent circuit of a common emitter amplifier is shown below. If the emitter area of the BJT is  $100\mu^2$  and the load resistor  $R_L$  is 2K, bias this circuit so that the quiescent output voltage is 5V and the DC voltage across  $R_L$  is also 5V while maintaining the same small signal gain that this circuit has. You have one dc power supply available of any value you choose and any number of resistors and capacitors.



**Problem 6** Consider the following circuit.

- a) Determine an analytical expression that relates  $I_{\text{OUT}}$  to  $I_{\text{IN}}$
- b) With a computer simulation, plot the relationship between  $I_{OUT}$  and  $I_{IN}$  as  $I_{IN}$  is varied between -40uA and +40uA .



**Problem 7** A Boolean System is supposed to have an output F that is high when the Boolean inputs A and B are high or when the inputs C and D are high and E is low or when the input A is low and the input E is high.

- a) Give a behavioral description of this system in terms of the input/output variables A,B,C,D,E, and F.
- b) Write Verilog code describing this system at the behavioral level
- c) Give a gate-level structural description of this system if the only gates that are NOR gates with any number of inputs
- d) Write Verilog code describing this system at the gate level
- e) Give a transistor-level physical description of this system. You may use any logic style you are familiar with. You need not size the devices

**Problem 8** Give two distinct structural implementations at the gate level of a system with the following Behavioral Description: The output F is high when A is high and B is high or when C is low and B is low. Otherwise the F output is low.